

NUMERICAL STUDY OF 10nm-SCALE MOSFET

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## **Abstract**

The proposed project is to design and develop a Numerical of 10nm-scale MOSFET. The aims of the project are to develop and simulate a theoretical and characteristics model that describes a MOSFET with channel length of 10nm.

This report contains with the background and research of the 10nm MOSFET.

The structure and block diagram of the proposed project, the objectives planned to be achieved included in this report.